WIGGLING CONTROL FOR PSEUDO-HARDMASK

ABSTRACT OF THE DISCLOSURE

A method for etching features in an etch layer. A conditioning for a patterned pseudo-hardmask of amorphous carbon or polysilicon disposed over the etch layer is provided, where the conditioning comprises providing a fluorine free deposition gas comprising a hydrocarbon gas, forming a plasma from the fluorine free deposition gas, providing a bias less than 500 volts, and forming a deposition on top of the patterned pseudo-hardmask. The etch layer is etched through the patterned pseudo-hardmask.

FIG.1

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